PATENT 81788.0026

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Seiichi Mori

Scrial No: 09/456,873

Filed: December 8, 1999

For: NON-VOLATILE SEMICONDUCTOR

MEMORY DEVICE

Art Unit: 2826

Examiner: L. Andujar

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office, Fax No. (703) 308-7382 on June 28, 2001.

Starlod A. Masof. Reg. No. 41.179 Name 27, 2001

RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents Washington, D.C. 20231

Attention: Box Amendment

Dear Sir:

In response to the Office Action mailed March 28, 2001, the three-month statutory period during which to respond thereto expiring June 28, 2001, Applicant submits the following amendments and remarks in the above-identified application.

AMENDMENT

FAX COPY RECEIVED

Please amend the above-identified application as indicated below.

JUN 26 2001

TECHNOLOGY CENTER 2800

IN THE SPECIFICATION:

Please amend the specification as indicated below.

Replace the paragraph starting on page 1, line 19 with the following text:

FIGS. 4A and 45 show sections, taken in two directions orthogonal to each other, of the memory cell structure described above. Normally in a flash memory, the control gate of a